NPN Plastic Silicon Power Transistor

 \dots designed for low power audio amplifier and low–current, high speed switching applications.

- High Collector–Emitter Sustaining Voltage VCEO(sus) = 100 Vdc (Min)
- High DC Current Gain @ I_C = 200 mAdc h_{FE} = 40–250
- Low Collector–Emitter Saturation Voltage —
 VCE(sat) = 0.5 Vdc (Max) @ IC = 500 mAdc
- High Current Gain Bandwidth Product —
 fT = 40 MHz (Min) @ I_C = 100 mAdc)

*MAXIMUM RATINGS

Rating	Symbol	Max	Unit
Collector–Emitter Voltage	VCEO	100	Vdc
Collector–Base Voltage	V _{CB}	100	Vdc
Emitter-Base Voltage	V _{EBO}	6.0	Vdc
Collector Current — Continuous — Peak	IC	4.0 8.0	Adc
Base Current	lΒ	1.0	Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	15 0.12	Watts W/°C
Operating and Storage Junction Temperature Range	T _J ,T _{Stg}	-65 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{ heta JC}$	8.34	°C/W

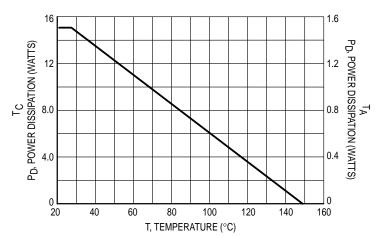


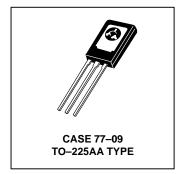
Figure 1. Power Derating

Preferred devices are Motorola recommended choices for future use and best overall value.

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Motorola Preferred Device

4 AMPERE
POWER TRANSISTOR
SILICON
100 VOLTS
15 WATTS





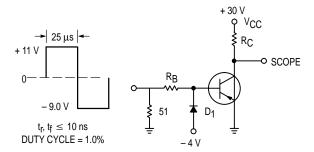
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*ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	•			•
Collector–Emitter Sustaining Voltage (1) (IC = 10 mAdc, IB = 0)	VCEO(sus)	100	_	Vdc
Collector Cutoff Current (VCE = 50 Vdc, I _B = 0)	ICEO	_	100	μAdc
Collector Cutoff Current (VCE = 100 Vdc, VBE(off) = 1.5 Vdc) (VCE = 50 Vdc, VBE(off) = 1.5 Vdc, TC = 125°C)	ICEX	_	1.0 0.1	μAdc mAdc
Emitter Cutoff Current (VEB = 6.0 Vdc, IC = 0)	I _{EBO}	_	1.0	μAdc
ON CHARACTERISTICS (1)	•			
DC Current Gain (I _C = 200 mAdc, V _{CE} = 3 0 Vdc) (I _C = 1.0 Adc, V _{CE} = 3.0 Vdc) (I _C = 2.0 Adc, V _{CE} = 3.0 Vdc) (I _C = 4.0 Adc, V _{CE} = 3.0 Vdc)	h _{FE}	40 20 10 5.0	250 — — —	_
Collector Emitter Saturation Voltage (I _C = 500 mAdc, I _B = 50 mAdc) (I _C = 1.0 Adc, I _B = 100 mAdc) (I _C = 2.0 Adc, I _B = 200 mAdc) (I _C = 4.0 Adc, I _B = 800 mAdc)	VCE(sat)	_ _ _ _	0.5 1.0 2.5 3.0	Vdc
Base–Emitter Saturation Voltage (I _C = 2.0 Adc, I _B = 200 mAdc)	V _{BE(sat)}	_	1.8	Vdc
Base–Emitter On Voltage (I _C = 200 mAdc, V _{CE} = 3.0 Vdc)	VBE(on)	_	1.5	Vdc
DYNAMIC CHARACTERISTICS	•			
Current–Gain — Bandwidth Product (I _C = 100 mAdc, V _{CE} = 10 Vdc, f = 10 MHz)	fΤ	40	_	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _C = 0, f = 0.1 MHz)	C _{ob}	_	50	pF
Small–Signal Current Gain (I _C = 200 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)	h _{fe}	10	_	_

^{*} Indicates JEDEC Registered Data.

⁽¹⁾ Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.



 R_B and R_C varied to obtain desired current levels D_1 must be fast recovery type, eg $$\rm MBR340$ used above IB ≈ 100 ma ${\rm MSD6100}$ used below IB ≈ 100 ma for PNP test circuit, reverse all Polarities.

Figure 2. Switching Time Test Circuit

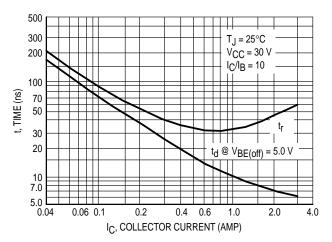


Figure 3. Turn-On Time

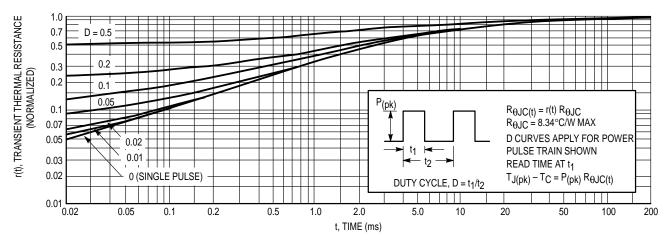


Figure 4. Thermal Response

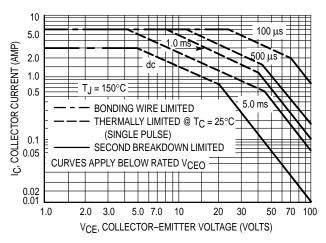


Figure 5. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_{\text{C}} - V_{\text{CE}}$ limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 150^{\circ}C$: T_{C} is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \le 150^{\circ}C$, $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

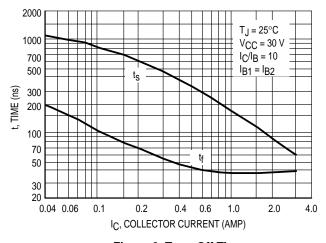


Figure 6. Turn-Off Time

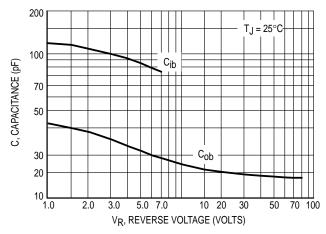
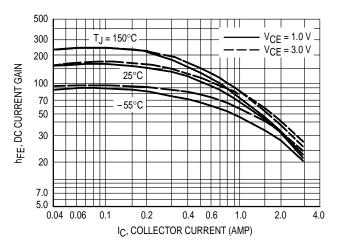


Figure 7. Capacitance

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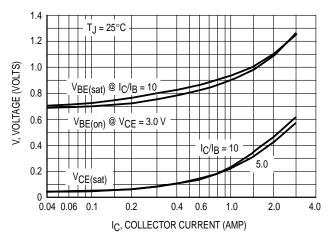


Figure 8. DC Current Gain

Figure 9. "On" Voltage

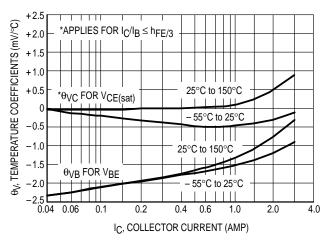
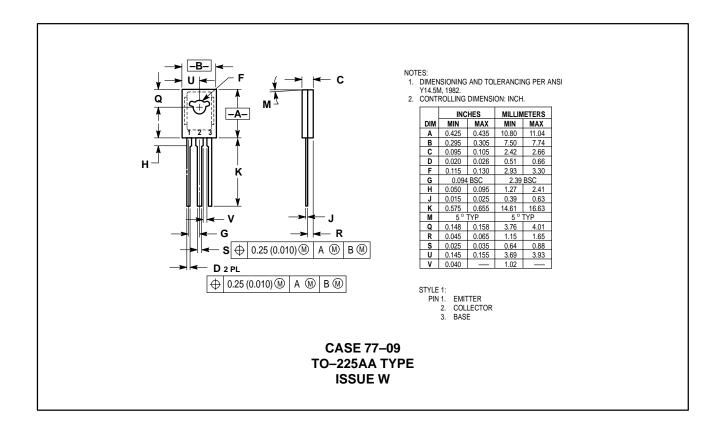


Figure 10. Temperature Coefficient

PACKAGE DIMENSIONS



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